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Press Contacts:

Eileen Elam
KJ Communications (in the U.S.)
Tel: +1 408 927-7753
eileen@kjcompr.com

Nick Foot
Billings PR (in Europe)
Tel: +44 1491 636393
nick.foot@billings-europe.com

Innovative Silicon's Z-RAM Receives *IEEE Spectrum Magazine's* Winning Technology Endorsement

Memory technology named a "Winner" in publication's January 2007 issue

SANTA CLARA, Calif., January 04, 2007— Innovative Silicon Inc. (ISi), the developer of Z-RAM® high density memory intellectual property (IP), announces it has been profiled as a winner in the semiconductor category in *IEEE Spectrum Magazine's* January 2007 issue. Each year the publication selects just five companies as "winners" and five others as "losers."

The IEEE Spectrum articles may be accessed on-line via these links:
<http://spectrum.ieee.org/jan07/4839> , and <http://spectrum.ieee.org/jan07/4830>.

"Being named by *IEEE Spectrum* as a winning company and 'Masters of Memory' is a huge testament to the contribution our Z-RAM memory makes to the industry, and to the vision of ISi as a provider a revolutionary memory technology," said Mark-Eric Jones, CEO of Innovative Silicon. "Moreover, we appreciate that the editors at *IEEE Spectrum*, who are experts in electronics technology, recognize the significance of our providing the highest density embedded memory implementation for SoCs and microprocessors."

Innovative Silicon has been the recipient of other prestigious awards. Editors at semiconductor trade magazine *EE Times* named ISi to its list of 60 Emerging Startups, which is better known as the "Silicon 60," each year since the list was created in early 2004. ISi was also awarded the "Best Invention of the Year" status by the Swiss Federal Institute of Technology (EPFL).

About Innovative Silicon

Innovative Silicon Inc. (ISi) delivers ultra high density memory IP for embedded SoC, MPU, and portable consumer applications. ISi's Z-RAM® technology provides up to twice the density of embedded DRAM and is five times denser than embedded SRAM, making it the world's lowest-cost

semiconductor memory solution. The company closed its first round of VC funding in 2003, completed its first 90nm megabit Z-RAM memory designs in 2004, its first 65nm designs in 2005 and its first 45nm designs in 2006. The company is incorporated in the USA with R&D in Lausanne, Switzerland. For more information see <http://www.z-ram.com>.

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